

2SD1264, 2SD1264A

Silicon NPN triple diffusion planar type

For low-frequency power amplification

For TV vertical deflection output

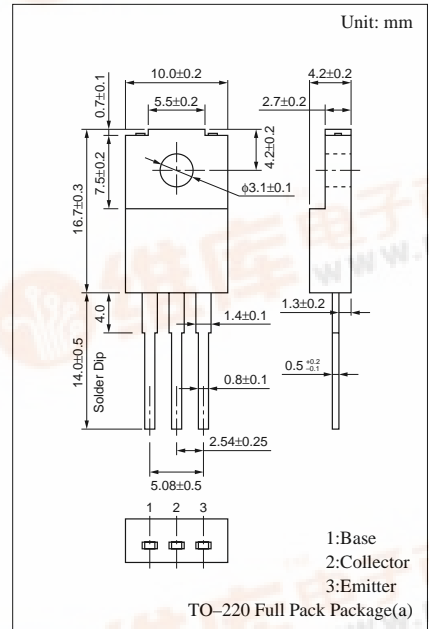
Complementary to 2SB940 and 2SB940A

Features

- High collector to emitter V_{CEO}
- Large collector power dissipation P_C
- Full-pack package which can be installed to the heat sink with one screw

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Rated	Unit
Collector to base voltage	V_{CBO}	200	V
Collector to emitter voltage	V_{CEO}	150	V
		180	
Emitter to base voltage	V_{EBO}	6	V
Peak collector current	I_{CP}	3	A
Collector current	I_C	2	A
Collector power dissipation	P_C	$T_C=25^\circ\text{C}$	W
		$T_a=25^\circ\text{C}$	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Electrical Characteristics ($T_C=25^\circ\text{C}$)

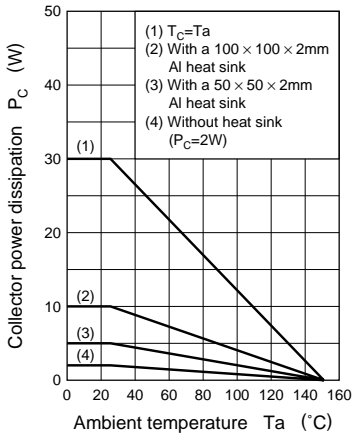
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 200\text{V}, I_E = 0$			50	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$			50	μA
Collector to base voltage	V_{CBO}	$I_C = 50\mu\text{A}, I_E = 0$	200			V
Collector to emitter voltage	V_{CEO}	$I_C = 5\text{mA}, I_B = 0$	150			V
			180			
Emitter to base voltage	V_{EBO}	$I_E = 500\mu\text{A}, I_C = 0$	6			V
Forward current transfer ratio	h_{FE1}	$V_{CE} = 10\text{V}, I_C = 150\text{mA}$	60		240	
		$V_{CE} = 10\text{V}, I_C = 400\text{mA}$	50			
Base to emitter voltage	V_{BE}	$V_{CE} = 10\text{V}, I_C = 400\text{mA}$			1	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			1	V
Transition frequency	f_T	$V_{CE} = 5\text{V}, I_C = 0.5\text{A}, f = 1\text{MHz}$		20		MHz

Rank Classification

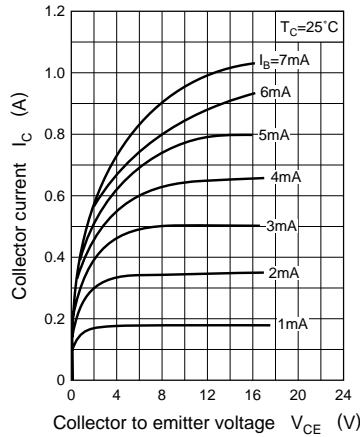
Rank	Q	P
h_{FE1}	60 to 140	100 to 240



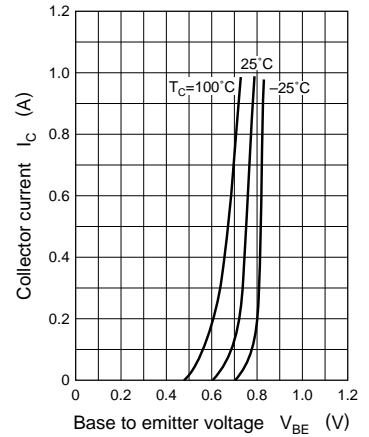
$P_C - T_a$



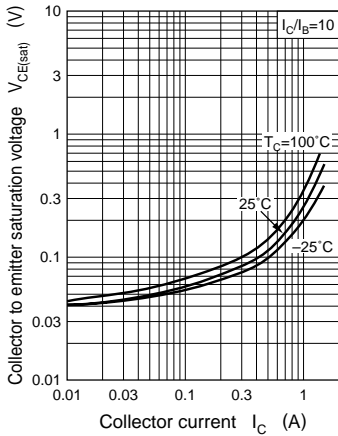
$I_C - V_{CE}$



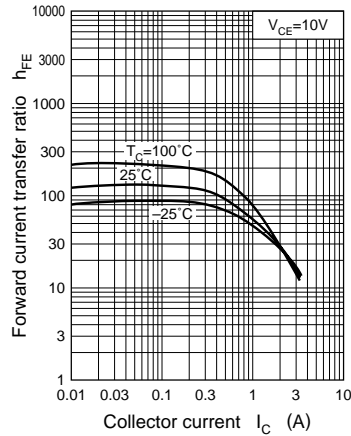
$I_C - V_{BE}$



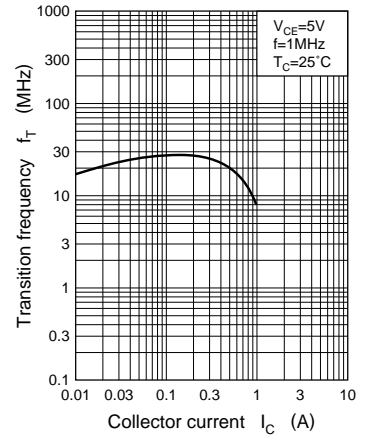
$V_{CE(sat)} - I_C$



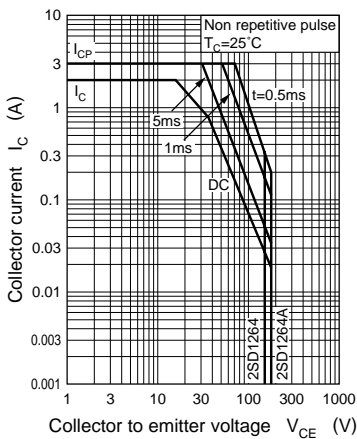
$h_{FE} - I_C$



$f_T - I_C$



Area of safe operation (ASO)



$R_{th(t)} - t$

